

# High voltage fast-switching NPN power transistor

Datasheet - production data

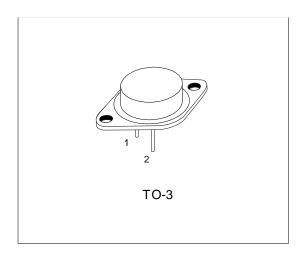
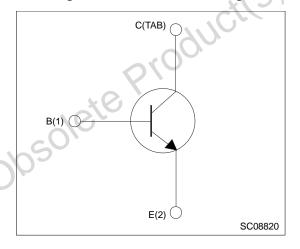


Figure 1: Internal schematic diagram



### **Features**

- NPN transistor
- High voltage capability
- High current capability
- Fast switching speed

## **Applications**

- Switched mode power supplies
- Flyback and forward single transistor low power converters

### Description

The 2N6547 is a high voltage Multiepitaxial Mesa NPN transistor mounted in a TO-3 metal case. It is particularly suited for switching and industrial applications from single and three-phase mains.

**Table 1: Device summary** 

Order code	Marking	Packages	Packaging
2N6547	2N6547	TO-3	Bag

Contents \_\_\_\_\_\_ 2N6547

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2N6547 Electrical ratings

# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CER</sub>	Collector-emitter voltage ( $R_{BE}$ = 50 $\Omega$ )	850	V
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0)	850	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	400	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	9	V
Ic	Collector current	15	Α
Ісм	Collector peak current	30	A
I <sub>B</sub>	Base current	10	Α
I <sub>BM</sub>	Base peak current	20	А
P <sub>TOT</sub>	Total dissipation at Tc = 25 °C	175	W
T <sub>STG</sub>	Storage temperature	-65 to 200	°C
T <sub>J</sub>	Max. operating junction temperature	200	°C

Table 3: Thermal data

	Symbol	Parameter	Value	Unit
	R <sub>thj-case</sub>	Thermal resistance junction-case max.	1	°C/W
	ate Pro	20.0		
Opso.				

**Electrical characteristics** 2N6547

### **Electrical characteristics** 2

**Table 4: Electrical characteristics** 

Parameter	Test conditions	Min.	Тур.	Max.	Unit
Collector cut-off current	V <sub>CE</sub> = 850 V			1	mA
(V <sub>BE</sub> = 0)	V <sub>CE</sub> = 850 V, Tc = 100 °C			4	mA
Collector cut-off current ( $R_{BE} = 10 \Omega$ )	V <sub>CE</sub> = 850 V, Tc = 100 °C			5	mA
Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 9 V			1	mA
Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	400	. \C		V
Collector-emitter saturation	I <sub>C</sub> = 10 A, I <sub>B</sub> = 2 A			1.5	V
voltage	I <sub>C</sub> = 15 A, I <sub>B</sub> = 3 A	0		5	V
	I <sub>C</sub> = 10 A, I <sub>B</sub> = 2 A, Tc = 100 °C			2.5	V
Base-emitter saturation	I <sub>C</sub> = 10 A, I <sub>B</sub> = 2 A			1.6	V
voltage	I <sub>C</sub> = 10 A, I <sub>B</sub> = 2 A, Tc = 100 °C			1.6	V
DC current gain	I <sub>C</sub> = 5 A, V <sub>CE</sub> = 2 V	12		30	
	I <sub>C</sub> = 10 A, V <sub>CE</sub> = 2 V	6			
Transition frequency	I <sub>C</sub> = 0.5 A, V <sub>CE</sub> = 10 V, f = 1 MHz		3		MHz
Collector-base capacitance (I <sub>E</sub> =0)	V <sub>CB</sub> = 10 V, f = 1 MHz			360	pF
t: pulse duration ≤ 300 μs, duty cy	cle ≤ 2%				1
	Collector cut-off current $(V_{BE} = 0)$ Collector cut-off current ( $R_{BE} = 10~\Omega$ ) Emitter cut-off current ( $I_{C} = 0$ ) Collector-emitter sustaining voltage ( $I_{B} = 0$ ) Collector-emitter saturation voltage  Base-emitter saturation voltage  DC current gain  Transition frequency  Collector-base capacitance ( $I_{E} = 0$ )	$ \begin{array}{c} \text{Collector cut-off current} & V_{\text{CE}} = 850 \text{ V} \\ V_{\text{CE}} = 850 \text{ V}, \text{ Tc} = 100 \\ ^{\circ}\text{C} \\ \end{array} $	$ \begin{array}{c} \text{Collector cut-off current} \\ (V_{BE} = 0 \hspace{1mm}) \\ (V_{CE} = 850 \hspace{1mm} V, Tc = 100 \\ ^{\circ}C \\ \end{array} $ $ \begin{array}{c} \text{Collector cut-off current (R_{BE} = 10 \hspace{1mm} 0)} \\ \text{Collector cut-off current (I_{C} = 0)} \\ \text{Emitter cut-off current (I_{C} = 0)} \\ \text{Collector-emitter sustaining voltage (I_{B} = 0)} \\ \text{Collector-emitter saturation voltage} \\ \end{array} $ $ \begin{array}{c} I_{C} = 100 \hspace{1mm} \text{MA} \\ I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} I_{B} = 2 \hspace{1mm} \text{A} \\ I_{C} = 15 \hspace{1mm} \text{A}, \hspace{1mm} I_{B} = 3 \hspace{1mm} \text{A} \\ I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} I_{B} = 2 \hspace{1mm} \text{A}, \hspace{1mm} \text{Transition frequency}} \\ \text{DC current gain} \\ \end{array} $ $ \begin{array}{c} I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} I_{B} = 2 \hspace{1mm} \text{A}, \hspace{1mm} \text{Transition frequency} \\ I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 2 \hspace{1mm} \text{V} \\ I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 2 \hspace{1mm} \text{V} \\ I_{C} = 10 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 10 \hspace{1mm} \text{V}, \hspace{1mm} f \\ I_{C} = 1 \hspace{1mm} \text{MHz} \\ \end{array} $ $ \begin{array}{c} I_{C} = 0.5 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 10 \hspace{1mm} \text{V}, \hspace{1mm} f \\ I_{C} = 1 \hspace{1mm} \text{MHz} \\ \end{array} $ $ \begin{array}{c} I_{C} = 0.5 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 10 \hspace{1mm} \text{V}, \hspace{1mm} f \\ I_{C} = 1 \hspace{1mm} \text{MHz} \\ \end{array} $ $ \begin{array}{c} I_{C} = 0.5 \hspace{1mm} \text{A}, \hspace{1mm} V_{CE} = 10 \hspace{1mm} \text{V}, \hspace{1mm} f \\ I_{C} = 1 \hspace{1mm} \text{MHz} \\ \end{array} $	$ \begin{array}{c} \text{Collector cut-off current} \\ (V_{\text{BE}} = 0 ) \\ \hline \\ \text{Collector cut-off current (R}_{\text{BE}} = \\ 10  \Omega) \\ \hline \\ \text{Emitter cut-off current (I}_{\text{C}} = 0) \\ \hline \\ \text{Collector-emitter sustaining} \\ \text{voltage (I}_{\text{B}} = 0) \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-emitter saturation} \\ \hline \\ \text{voltage} \\ \hline \\ \hline \\ \text{Collector-mitter saturation} \\ \hline \\ \text{Voltage} \\ \hline \\ \hline \\ \text{Collector-pain} \\ \hline \\ \hline \\ \text{Collector-passe capacitance} \\ \hline \\ \text{Collector-base capacitance} \\ \hline \\ \hline \\ \text{Volume} \\ \hline \\ \text{Volume} \\ \hline \\ \text{Volume} \\ \hline \\ \text{Collector-base capacitance} \\ \hline \\ \text{Volume} \\ \hline \\ \text{Volume} \\ \hline \\ \text{Volume} \\ \hline \\ \text{Collector-base capacitance} \\ \hline \\ \text{Volume} \\ \hline \\ Volu$	$ \begin{array}{c} \text{Collector cut-off current} \\ \text{($V_{\text{BE}}$ = 0$)} \\ \text{Collector cut-off current ($R_{\text{BE}}$ = } \\ 10 \ \Omega\text{)} \\ \text{Collector cut-off current ($R_{\text{C}}$ = 0)} \\ \text{Collector-emitter sustaining} \\ \text{voltage ($I_{\text{B}}$ = 0)} \\ \text{Collector-emitter sustaining} \\ \text{voltage ($I_{\text{B}}$ = 0)} \\ \text{Collector-emitter saturation} \\ \text{voltage} \\ \text{Ic} = 100 \ \text{mA} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A} \\ \text{Ic} = 15 \ \text{A, } I_{\text{B}} = 3 \ \text{A} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A, } \text{Tc} = \\ 100 \ \text{°C} \\ \text{Collector-emitter saturation} \\ \text{voltage} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A, } \text{Tc} = \\ 100 \ \text{°C} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A, } \text{Tc} = \\ 100 \ \text{°C} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A, } \text{Tc} = \\ 100 \ \text{°C} \\ \text{Ic} = 10 \ \text{A, } I_{\text{B}} = 2 \ \text{A, } \text{Tc} = \\ 100 \ \text{°C} \\ \text{Ic} = 10 \ \text{A, } I_{\text{C}} = 10 \ \text{A, } \text{Ic} = 10 \ \text$

Table 5: Resistive load

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
ton	Turn-on time	V <sub>CC</sub> = 250 V, I <sub>C</sub> = 10 A	-	-	1	μs
ts	Storage time	$I_{B1} = -I_{B2} = 2 \text{ A}, T_p \ge 25 \mu\text{s}$	-	-	4	μs
t <sub>f</sub>	Fall time		-	-	0.7	μs

Table 6: Inductive load

	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	ts	Storage time	$V_{CL} = 450 \text{ V}, I_{C} = 10 \text{ A}, L_{C} = 180 \text{ mH}, I_{B1} = 2$ A, $V_{BE} = -5 \text{ V}, T_{C} = 100 ^{\circ}\text{C}$	-	j	5	μs
	t <sub>f</sub>	Fall time		0	. (	1.5	μs
Obsola	ate F	rodiu	ct(s)				

## 3 Package information

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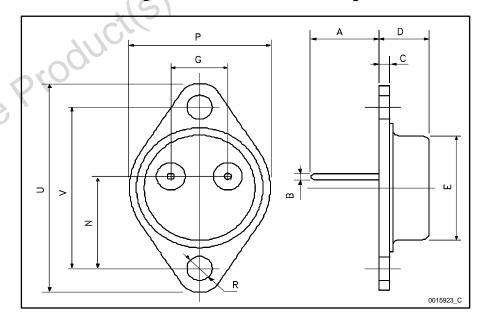


## 3.1 TO-3 mechanical data

Table 7: TO-3 mechanical data

Dim.	mm				
	Min.	Тур.	Max.		
Α	11.00		13.10		
В	0.97		1.15		
С	1.50		1.65		
D	8.32	-	8.92		
Е	19.00		20.00		
G	10.70		11.10		
N	16.50		17.20		
Р	25.00	01/	26.00		
R	4.00	*6,	4.09		
U	38.50	16/	39.30		
V	30.00	0,	30.30		

Figure 2: TO-3 mechanical data drawing



Revision history 2N6547

# 4 Revision history

**Table 8: Revision history** 

Date	Revision	Changes
12-Dec-2012	3	Changed $F_T$ value in electrical characteristics table.



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